

INC6005AC1

FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON NPN EPITAXIAL TYPE

DESCRIPTION

INC6005AC1 is a silicon NPN transistor.
It is designed with high voltage.

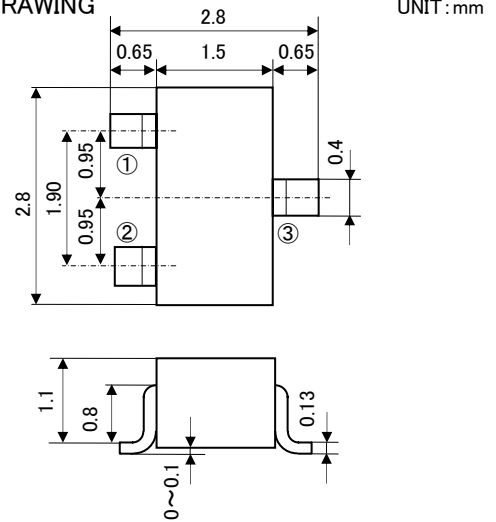
FEATURE

- Super mini package for easy mounting
- High voltage $V_{CE0}=400V$

APPLICATION

DC/DC convertor, High voltage switching

OUTLINE DRAWING



Terminal Connector

JEITA:SC-59

①: Base

JEDEC: Similar to TO-236

②: Emitter

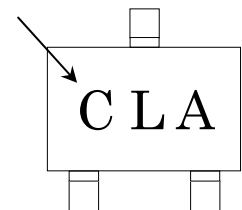
③: Collector

MAXIMUM RATING ($T_a=25^\circ C$)

| SYMBOL | PARAMETER | RATING | UNIT |
|-----------|---|----------|------------|
| V_{CBO} | Collector to Base voltage | 400 | V |
| V_{EBO} | Emitter to Base voltage | 7 | V |
| V_{CEO} | Collector to Emitter voltage | 400 | V |
| I_C | Collector current | 100 | mA |
| P_C | Collector dissipation($T_a=25^\circ C$) | 200 | mW |
| T_j | Junction temperature | +150 | $^\circ C$ |
| T_{stg} | Storage temperature | -55~+150 | $^\circ C$ |

MARKING

Type Name



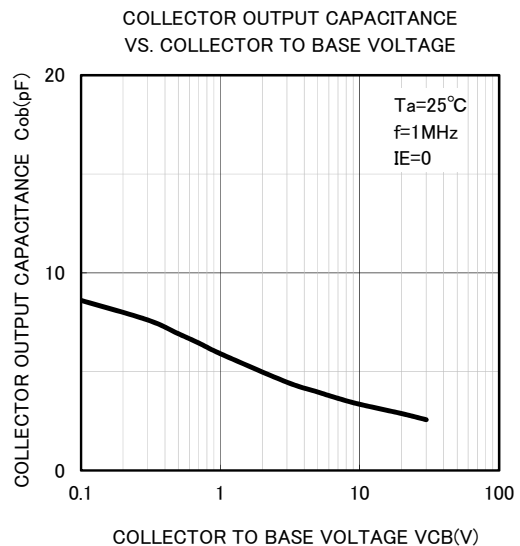
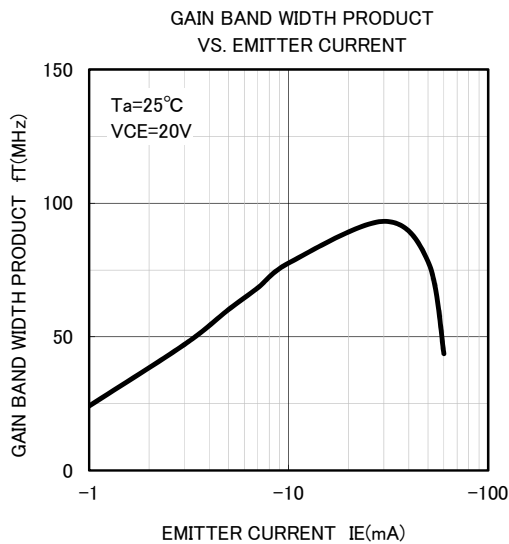
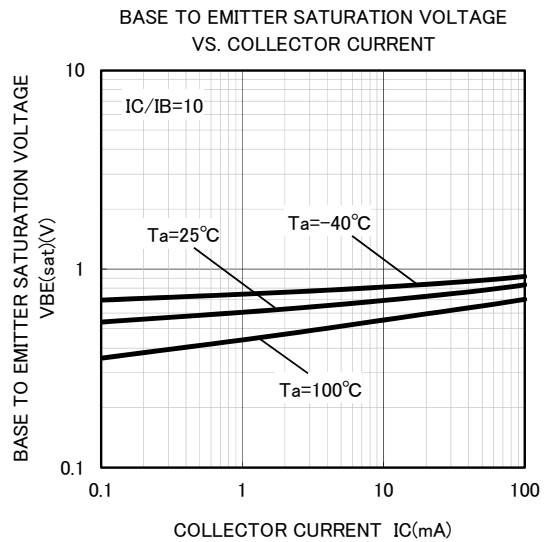
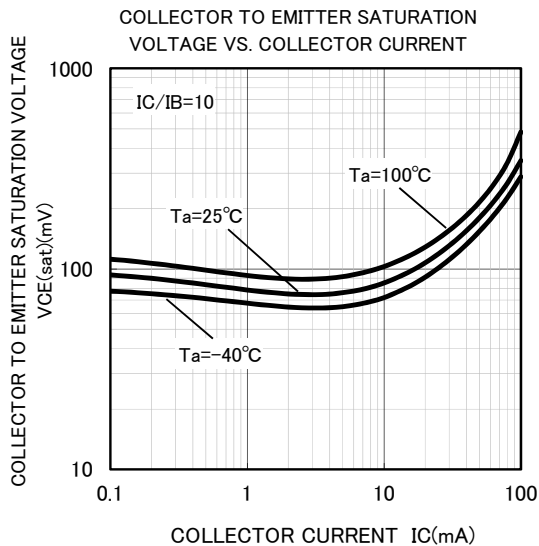
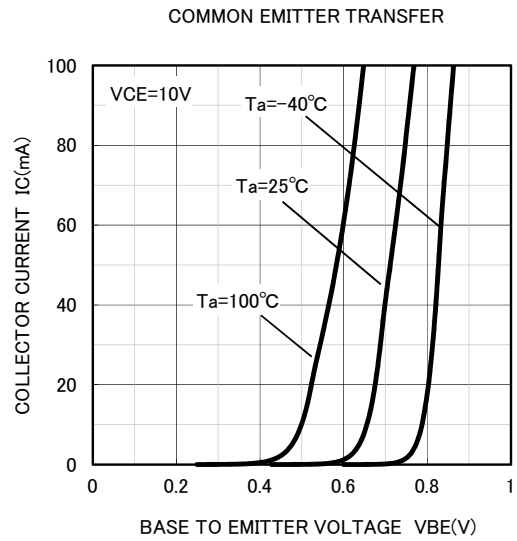
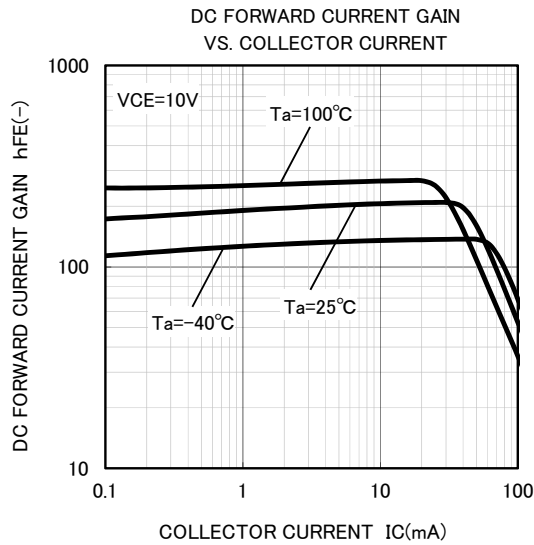
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

| SYMBOL | PARAMETER | TEST CONDITIONS | LIMITS | | | UNIT |
|---------------|------------------------------|-----------------------------------|--------|-----|-----|---------|
| | | | MIN | TYP | MAX | |
| $V_{(BR)CBO}$ | C to B break down voltage | $I_C=50 \mu A, I_E=0mA$ | 400 | - | - | V |
| $V_{(BR)EBO}$ | E to B break down voltage | $I_E=50 \mu A, I_C=0mA$ | 7 | - | - | V |
| $V_{(BR)CEO}$ | C to E break down voltage | $I_C=1mA, R_{BE}=\infty$ | 400 | - | - | V |
| I_{CBO} | Collector cut off current | $V_{CB}=400V, I_E=0mA$ | - | - | 1 | μA |
| I_{EBO} | Emitter cut off current | $V_{EB}=6V, I_C=0mA$ | - | - | 1 | μA |
| h_{FE} | DC forward current gain | $V_{CE}=10V, I_C=1mA$ | 82 | - | 280 | - |
| $V_{CE(sat)}$ | C to E saturation voltage | $I_C=10mA, I_B=1mA$ | - | - | 0.5 | V |
| f_T | Gain bandwidth product | $V_{CE}=20V, I_E=-10mA, f=100MHz$ | - | 70 | - | MHz |
| C_{ob} | Collector output capacitance | $V_{CB}=10V, I_E=0mA, f=1MHz$ | - | 3.3 | - | pF |

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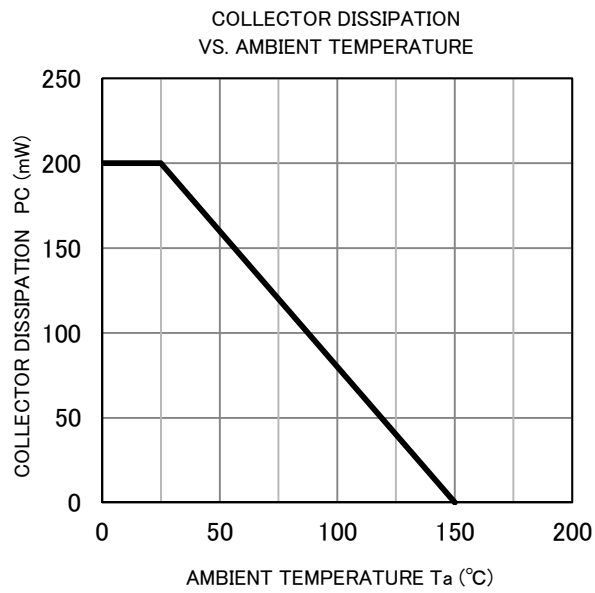
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TYPICAL CHARACTERISTICS



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SILICON NPN EPITAXIAL TYPE





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